





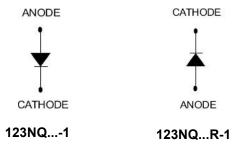
123NQ080/R-1 123NQ100/R-1 SCHOTTKY RECTIFIER



Features

- 175℃ T_J operation
- Unique high power, Half-Pak module
- Replaces three parallel DO-5'S
- Easier to mount and lower profile than DO-5'S
- High purity, high temperature epoxy encapsulation for enhanced
- mechanical strength and moisture resistance
- Low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- Base plate: Nickel plated; Terminals: Nickel plated
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram



Applications

- Switching power supply
- Converters
- Free-Wheeling diodes
- **Reverse battery protection**

The top side is terminal, the bottom side is base plate.

Maximum Ratings(limiting values, at 25 °C unless otherwise specified)

Characteristics	Symbol	Condition	Max.		Units
Peak Repetitive Reverse Voltage	V _{RRM}	-	80 123NQ080(R)-1		
Working Peak Reverse Voltage DC Blocking Voltage	$egin{array}{c} V_{RWM} \ V_{R} \end{array}$		100 123NQ100(R)-1		- V
Average Forward Current	I _{F(AV)}	50% duty cycle @Tc=133°C, rectangular wave form		120	Α
Peak One Cycle Non-Repetitive Surge Current	I _{FSM}	8.3 ms, half Sine pulse	2520		А
Non-Repetitive Avalanche Energy	E _{AS}	T _J =25℃,I _{AS} =1A,L=30mH	15		mJ
Repetitive Avalanche Current	I _{AR}	Current decaying linearly to zero in 1 μ sec Frequency limited by T_J max. V_A =1.5 \times V_R typical	1		А

- China Germany Korea Singapore United States
 - http://www.smc-diodes.com sales@ smc-diodes.com •







Electrical Characteristics:

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop*	V _{F1}	@ 120A, Pulse, T_J = 25 °C@ 240A, Pulse, T_J = 25 °C	0.82 0.91	0.91 1.08	V
	V _{F2}	@ 120A, Pulse, T _J = 125 °C @ 240A, Pulse, T _J = 125 °C	0.71 0.80	0.74 0.88	V
Reverse Current*	I _{R1}	@V _R = rated V _R T _J = 25 °C	0.6	3000	uA
	I _{R2}	$@V_R = \text{rated } V_R T_J = 125 ^{\circ}\text{C}$	0.2	40	mA
Junction Capacitance	Ст	$@V_R = 5V, T_C = 25 °C$ $f_{SIG} = 1MHz$	2674	3000	pF
Max. Voltage Rate of Change	dv/dt	-	-	10,000	V/μs

 $^{^*}$ Pulse width < 300 μ s, duty cycle < 2%

Thermal-Mechanical Specifications:

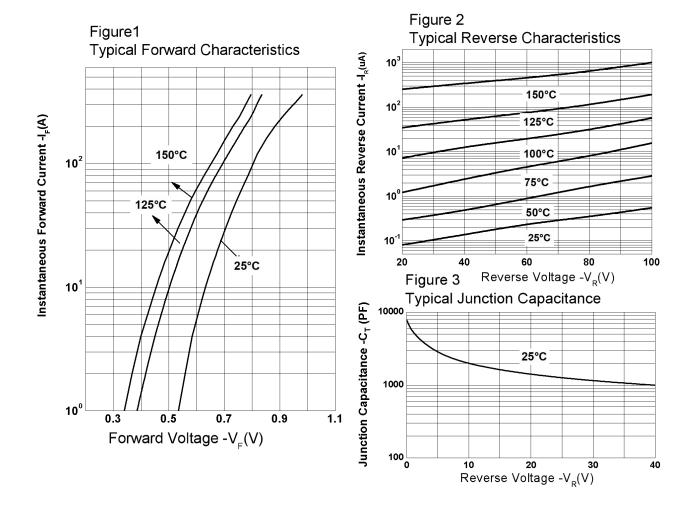
Characteristics	Symbol	Condition	Specification		Units
Junction Temperature	TJ	-	-55 to +175		°C
Storage Temperature	T _{stg}	-	-55 to +175		°C
Typical Thermal Resistance Junction to Case	R ₀ JC	DC operation	0.25		°C/W
Typical Thermal Resistance, case to Heat Sink	R _{θcs}	Mounting surface, smooth and greased	0.07		°C/W
Mounting Torque	T _M	Non-lubricated threads	Mounting Torque Terminal Torque	23(min) 29(max) 35(min) 46(max)	Kg-cm
Approximate Weight	wt	-	36		g
Case Style	PRM1-1				







Ratings and Characteristics Curves



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Ordering Information

Device	Package	Shipping	
123NQ SERIES	PRM1-1(Pb-Free)	27pcs/ box	

Marking Diagram

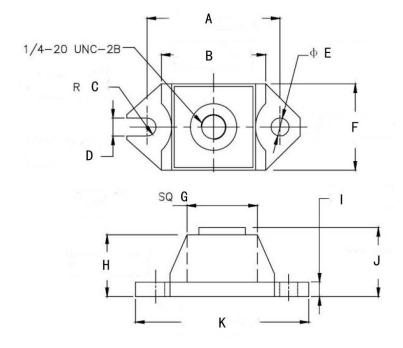
SS XXXX 123NQ080-1 Where XXXX is YYWW

1st row SS YYWW 2nd row 123NQ080-1 SS = SS = Year WW = Week

Cautions: Molding resin

Epoxy resin UL:94V-0

Mechanical Dimensions PRM1-1 (Inches/Millimeters)



SYMBOL	Millimeters		Inches		
	Min.	Max.	Min.	Max.	
Α	29.35	30.95	1.155	1.219	
В	24.77	26.04	0.975	1.026	
С	1.79	2.19	0.070	0.087	
D	3.73	4.24	0.146	0.167	
Е	3.73	4.24	0.146	0.167	
F	18.42	19.69	0.725	0.775	
G	18.55	19.55	0.730	0.770	
Н	13.59	14.47	0.535	70.500	
I	3.05	3.90	0.120	0.154	
J	14.87	15.87	0.585	0.625	
К	38.61	39.62	1.520	1.560	







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